

PNP Epitaxial Silicon Transistor

KSA1015

Features

- Low-Frequency Amplifier
- Collector-Base Voltage: $V_{CBO} = -50\text{ V}$
- Complement to KSC1815
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

ABSOLUTE MAXIMUM RATINGS ($T_A = 25\text{ }^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-50	V
V_{CEO}	Collector-Emitter Voltage	-50	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current	-150	mA
I_B	Base Current	-50	mA
T_J	Junction Temperature	150	$^{\circ}\text{C}$
T_{STG}	Storage Temperature Range	-55 to 150	$^{\circ}\text{C}$

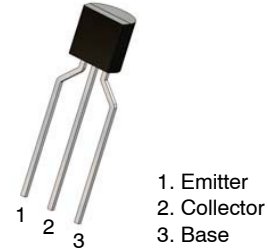
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS (Note 2)

($T_A = 25\text{ }^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Max	Unit
P_D	Total Device Dissipation	400	mW
	Derate Above $25\text{ }^{\circ}\text{C}$	3.2	mW/ $^{\circ}\text{C}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	312	$^{\circ}\text{C}/\text{W}$

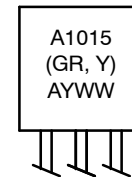
2. PCB size: FR-4, 76 mm x 114 mm x 1.57 mm (3.0 inch x 4.5 inch x 0.062 inch) with minimum land pattern size.



Bent Lead
Tape & Reel
Ammo Packing

TO-92 3 4.83x4.76 LEADFORMED
CASE 135AR

MARKING DIAGRAM



A = Assembly Site
A1015(GR, Y) = Device Code
Y = Year of Production,
WW = Work Week Number

ORDERING INFORMATION

Device	Marking	Package	Packing Method
KSA1015YTA	A1015Y	TO-92 3L (Pb-Free)	Ammo

DISCONTINUED (Note 1)

KSA1015GRTA	A1015GR	TO-92 3L (Pb-Free)	Ammo
-------------	---------	--------------------	------

1. **DISCONTINUED:** This device is not available. Please contact your onsemi representative for information. The most current information on this device may be available on www.onsemi.com.

ELECTRICAL CHARACTERISTICS ($T_A = 25\text{ }^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
BV_{CBO}	Collector-Base Breakdown Voltage	$I_C = -100\text{ }\mu\text{A}$, $I_E = 0$	-50	-	-	V
BV_{CEO}	Collector-Emitter Breakdown Voltage	$I_C = -10\text{ mA}$, $I_B = 0$	-50	-	-	V
BV_{EBO}	Emitter-Base Breakdown Voltage	$I_E = -10\text{ }\mu\text{A}$, $I_C = 0$	-5	-	-	V
I_{CBO}	Collector Cut-Off Current	$V_{CB} = -50\text{ V}$, $I_E = 0$	-	-	-0.1	μA
I_{EBO}	Emitter Cut-Off Current	$V_{EB} = -5\text{ V}$, $I_C = 0$	-	-	-0.1	μA
h_{FE1}	DC Current Gain	$V_{CE} = -6\text{ V}$, $I_C = -2\text{ mA}$	70	-	400	
h_{FE2}	DC Current Gain	$V_{CE} = -6\text{ V}$, $I_C = -150\text{ mA}$	25	-	-	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = -100\text{ mA}$, $I_B = -10\text{ mA}$	-	-0.1	-0.3	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C = -100\text{ mA}$, $I_B = -10\text{ mA}$	-	-	-1.1	V
f_T	Current Gain Bandwidth Product	$V_{CE} = -10\text{ V}$, $I_C = -1\text{ mA}$	80	-	-	MHz
C_{ob}	Output Capacitance	$V_{CB} = -10\text{ V}$, $I_E = 0$, $f = 1\text{ MHz}$	-	4	7	pF
NF	Noise Figure	$V_{CE} = -6\text{ V}$, $I_C = -0.1\text{ mA}$, $f = 100\text{ Hz}$, $R_G = 10\text{ k}\Omega$	-	0.5	6	dB

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

 h_{FE} CLASSIFICATION

Classification	O	Y	GR
h_{FE1}	70~140	120~240	200~400

TYPICAL PERFORMANCE CHARACTERISTICS

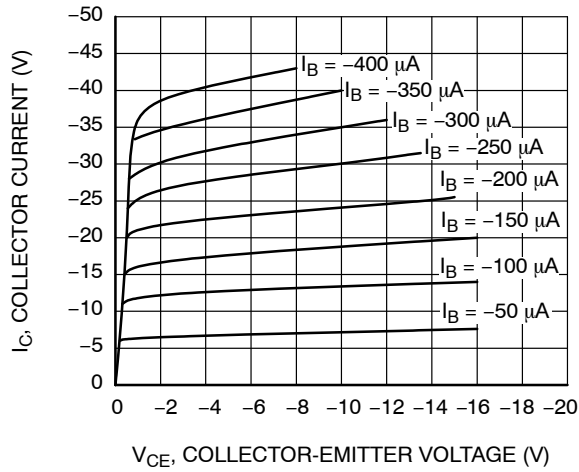


Figure 1. Static Characteristic

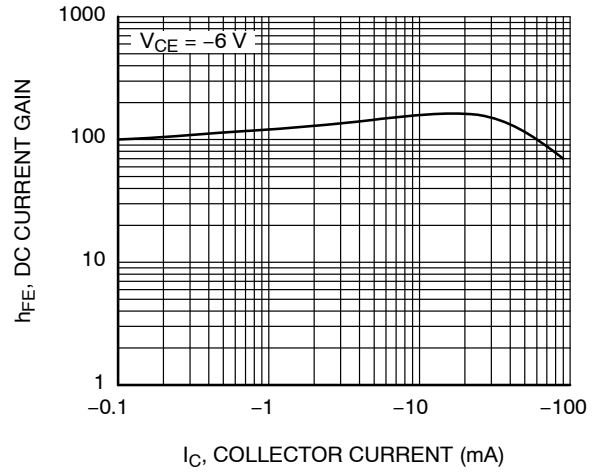


Figure 2. DC Current Gain

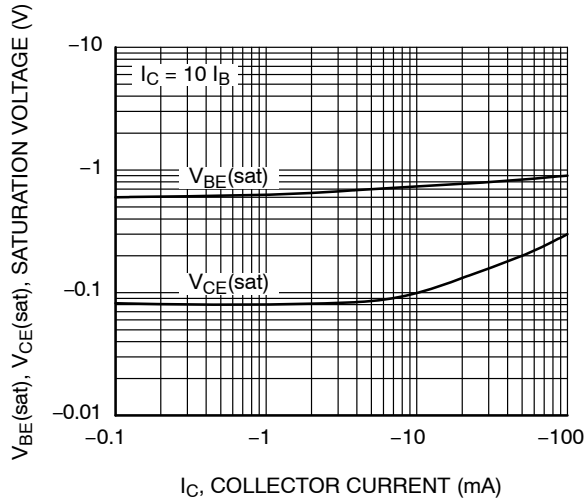


Figure 3. Base-Emitter Saturation Voltage and Collector-Emitter Saturation Voltage

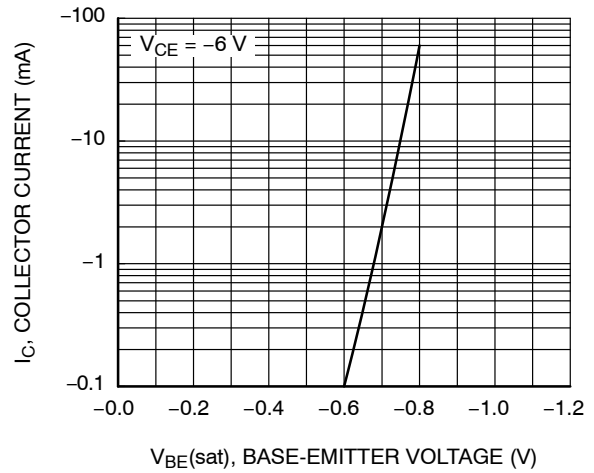


Figure 4. Base-Emitter On Voltage

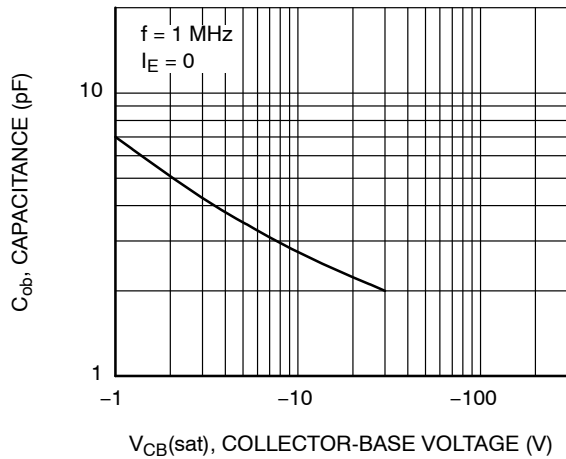


Figure 5. Collector Output Capacitance

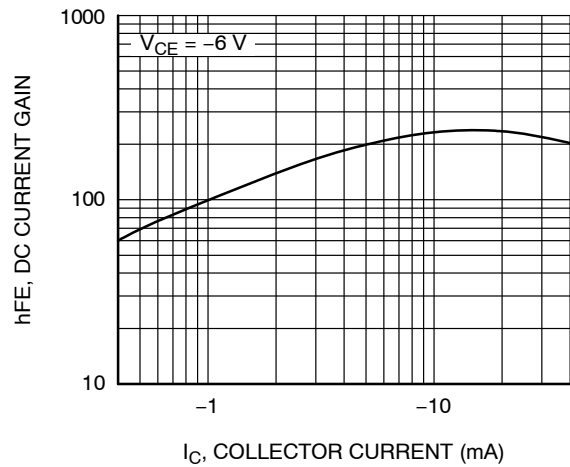


Figure 6. Current Gain Bandwidth Product

KSA1015

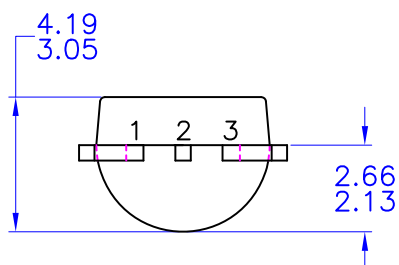
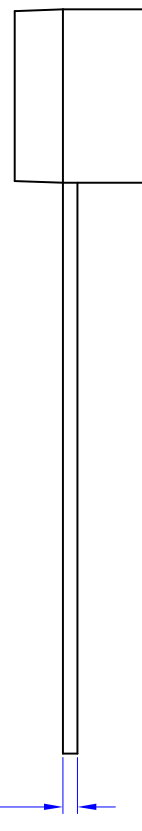
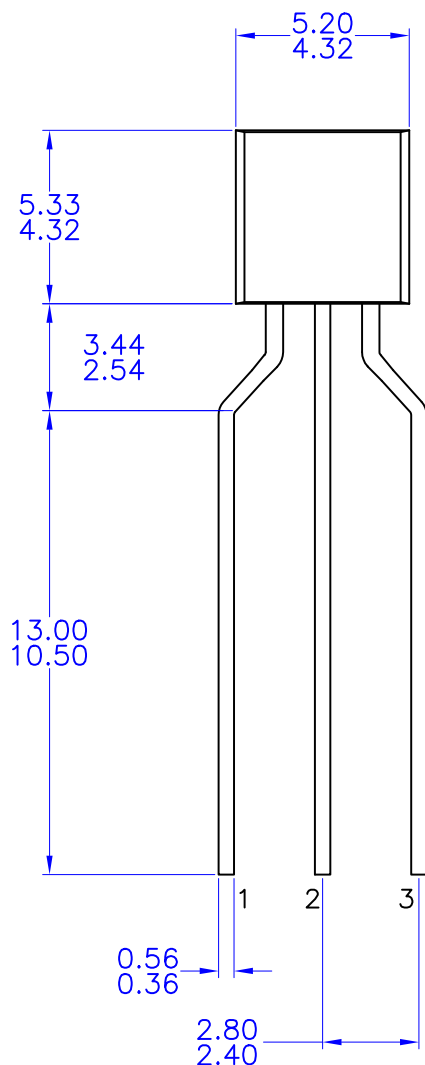
REVISION HISTORY

Revision	Description of Changes	Date
3	KSA1015GRTA OPN Marked as Discontinued.	11/11/2025

This document has undergone updates prior to the inclusion of this revision history table. The changes tracked here only reflect updates made on the noted approval dates.

TO-92 3 4.83x4.76 LEADFORMED
CASE 135AR
ISSUE O

DATE 30 SEP 2016



NOTES: UNLESS OTHERWISE SPECIFIED

- A) DRAWING WITH REFERENCE TO JEDEC TO-92 RECOMMENDATIONS.
- B) ALL DIMENSIONS ARE IN MILLIMETERS.
- C) DRAWING CONFORMS TO ASME Y14.5M-1994

DOCUMENT NUMBER:	98AON13879G	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
DESCRIPTION:	TO-92 3 4.83X4.76 LEADFORMED	PAGE 1 OF 1

onsemi and onsemi are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.